# Antiferromagnetism in the  $\text{Dy}_5\text{Ir}_4\text{Si}_{10}$  system

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In this paper we report the dc susceptibility and resistivity studies of the antiferromagnet  $Dy_5Ir_4Si_{10}$ . We find that this compound undergoes an antiferromagnetic transition at 5.0 K and the effective magnetic moment observed is  $10.6\mu_B$ , which is equal to the free-ion value for the Dy atom. However, the resistivity shows a broad minimum at 17 K and a maximum at 6.<sup>5</sup> K before it decreases below 6 K. We attribute this behavior of the resistivity to magnetic superzone effects in this compound.

## I. INTRODUCTION

Most of the studies on the coexistence of superconductivity and magnetism are made either on  $R\text{Mo}_{6}\text{S}_{8}$  chalcogenides or on the  $RRh_4B_4$  borides (R is a rare-earth element).<sup>1</sup> In these systems the superconductivity arises due to Mo clusters and Rh clusters, respectively, while magnetism is due to the rare-earth element. In the case of ternary silicides  $\text{Dy}_5 \text{Ir}_4 \text{Si}_{10}$  (Ref. 2) (where there are no clusters and no direct transition-metal-transition-metal contact), it is of interest to study the nature of the magnetism displayed by the rare-earth element. With this motivation, we have studied the previously reported (only  $T_N$ , the antiferromagnetic transition temperature)  $\text{Dy}_5 \text{Ir}_4 \text{Si}_{10}$  compound. We not only confirm the antiferromagnetic (AF) transition but also determine an effective-magnetic-moment value of  $10.6\mu_B$ , which is equal to the free-ion value of Dy. Furthermore, we also found that the resistivity  $(\rho)$  shows a broad minimum at 17 K and rises up to 6.5 K before it decreases below 6 K, signifying magnetic superzone effects in this compound.

#### II. EXPERIMENTAL DETAILS

The sample  $Dy_5Ir_4Si_{10}$  was made by melting the individual constituents in an arc furnace under high-purity argon atmosphere. The purity of Dy and Ir is 99.9% while that of Si is 99.999%. The sample was found to have the

4.000 4.00 s.500- ~ ~ 3.500— 3.000 E 3.000— 2.500 2.500 2.000  $\cdot$  . 2.000 1.500 <del>| | | | | | | | | | | |</del> | SCEPTIB 1.500-- 0 4 8 12 16 20 24 28 32 OO 1.000-- OO 0.500 m . . . . . . . . . . . . 0.000 30 60 90 120 150 180 210 240 270 300  $120$ TEMPERATURE(K)

FIG. 1. Variation of susceptibility  $\chi$  of Dy<sub>5</sub>Ir<sub>4</sub>Si<sub>10</sub> from 2 to 300 K. The inset shows  $\chi$  from 2 to 30 K.

tetragonal structure of the type  $PM3N$  (Sc<sub>5</sub>Co<sub>4</sub>Si<sub>10</sub> struc ture) and the lattice constants  $a$  and  $c$  agree with the previously published values.<sup>2</sup> The temperature dependence of susceptibility  $(y)$  was measured using a Quantum Design SQUID magnetometer in a field of <sup>1</sup> kOe from 2 to 300 K. The resistivity was measured using a fourprobe dc technique and the contacts were made using ultrasonic solder (with indium) on a cylindrical sample of 2 mm diameter and 10 mm length. The temperature was measured using a calibrated Si diode (LAKE SHORE) sensor. The sample voltage was measured with a Keithley nanovoltmeter with a current of 25 mA using a 20 ppm stable HP current source.

#### III. RESULTS AND DISCUSSION

### A. Susceptibility studies

The temperature dependence of  $\chi$  of  $Dy_5Ir_4Si_{10}$  from 2 to 300 K is shown in Fig. 1. The temperature dependence of  $\chi$  from 2 to 30 K is shown in the inset. One can observe the AF state around 5.0 K where  $\left(\frac{dy}{dT}\right)$  shows a maximum. The high-temperature  $\chi$  (100 K < T < 300 K) data are well fitted by the Curie-Weiss law  $[\chi(T)=C/(T-\Theta_N)]$ , which is shown in Fig. 2. The value of  $\Theta_N$  from this fit is 16 K which is higher than the  $T_N$  value. Further, the effective magnetic moment calcu-







FIG. 3. Temperature dependence of  $\rho(T)$  of Dy<sub>5</sub>Ir<sub>4</sub>Si<sub>10</sub> from 2 to 300K.

lated ( $\mu_{\text{eff}} = \sqrt{8C}$ ) from this data is 10.6 $\mu_B$ , which agrees with the free-ion value of Dy,  $10.63\mu_B$ .

#### B. Resistivity studies

The temperature dependence of resistivity  $(\rho)$  from 2 to 300 K is shown in Fig. 3. The low temperature  $\rho$  (2)  $K < T < 50$  K) is shown in Fig. 4. Here we find a broad minimum in  $\rho$  at 17 K then it rises up to 6.5 K and decreases. Such a minimum has been seen in many antiferromagnetic rare-earth metals $3-5$  and arises due to magnetic superzone effects. In the case of rare-earth metals such as Dy the resistivity shows a minimum followed by a maximum along the c axis before it decreases due to antiferromagnetic ordering.<sup>5</sup> This has been attributed to the magnetic superzone effect which arises because of the fact that the antiferromagnetic phase has a periodic arrangement along the c axis which is incommensurate with that of the lattice. However, such effects are not reported in intermetallic compounds. Only one paper<sup>6</sup> has observed this effect in substituted samples but not on an antiferromagnetic compound such as  $Dy_5Ir_4Si_{10}$ . If one assumes the oscillatory nature of 4f spins, the conduction electrons will experience a periodic potential whose period is incommensurate with that of the crystal lattice.



FIG. 4. Temperature dependence of  $\rho(T)$  of  $Dy_5Ir_4Si_{10}$  from 2 to 50K.

This periodic potential, together with that of the lattice, produces gaps in the energy dispersion of conduction electrons. The magnetic superzone effect occurs when such a gap opens above  $T_N$ , leading to the reduction in carrier density, hence  $\rho$  shows a maximum, followed by a decrease in  $\rho$  below  $T_N$  due to a reduction in the spinfluctuation scattering. Although our sample is a polycrystalline one, we see the magnetic superzone effect clearly in our compound. However, to compare with the theory it is essential to perform transport measurements in a single crystal of  $Dy_5Ir_4Si_{10}$  and also the neutrondiffraction study to determine the reduced magnetic moment.

#### IV. CONCLUSION

We have established the AF state in  $Dy_5Ir_4Si_{10}$  using dc susceptibility and resistivity measurements. The effective moment is equal to that of the free Dy ion. However,  $\rho(T)$  data show a broad minimum at 17 K followed by a maximum at 6.5 K before starting to decrease below 6 K. It will be interesting to perform neutrondiffraction measurements on the single crystal of this sample which will determine the crystal-field levels and the actual magnetic moment carried by Dy.

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